

SEMICONDUCTORS-DISCRETES

PartNo.	ProductNo.	Manuf.	Description	技術指標
23877	QM5HL-24	MITSUBISHI	Transistor Module	5 A 1200Vcbo
16535	QM75DY-H	MITSUBISHI	HIGHPOWER SWITCHING USE INSULATED TYPE	75A/600V/2U

其他系列電晶體

Other Series Transistors

詳細產品規格--請點擊www.100y.com.tw

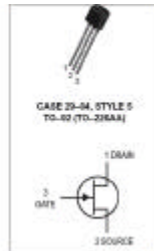
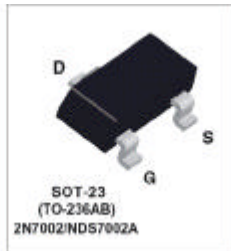
PartNo.	ProductNo.	Manuf.	Description	PoI	Ic(max)	Pc(max)	Vceo(max)	hfe(min.-max.)	Pins/Package
24061	2PC945P	PHILIPS	NPN general purpose transistor	NPN	100mA	500mW	50V	200~400	TO-92
24069	2PD601AS	PHILIPS	NPN general purpose transistor	NPN	100mA	250mW	50V	290~460	SOT-346
23362	BSS44	ST(SGS)	SWITCHING TRANSISTOR AND DARLINGTON	PNP	5A	5 W	60V		3P/TO-39
22611	HPH2369	HSMC	NPN EPITAXIAL PLANAR TRANSISTOR	NPN	500mA	625mW	15V	40~120	3P/TO-92
22620	IMZ1A	ROHM	General purpose transistor	PNP	-150mA	300mW	-50V	120~560	6P/SMT6
22645	KTC9013H	KEC	EPITAXIAL PLANAR NPN TRANSISTOR	NPN	500mA	625mW	30V	64~246	3P/TO-92
22647	KTC9014C	KEC	EPITAXIAL PLANAR NPN TRANSISTOR	NPN	150mA	625mW	50V		3P/TO-92
22646	KTC9015C	KEC	EPITAXIAL PLANAR PNP TRANSISTOR	PNP	-150mA	625mW	-50V	60~600	3P/TO-92
27005	MPQ3904	QUAD	AMPLIFIER SWITCHING TRANSISTOR	PNP					14P/DIP
25775	MPQ3906	QUAD	AMPLIFIER SWITCHING TRANSISTOR	PNP	-200mA	500mW	-40V	40~160	14P/DIP
22805	PMBT2907A	PHILIPS	PNP switching transistors	PNP	-600mA	250mW	-60V	50	3P/SOT-23
22806	PMBT3904	PHILIPS	NPN switching transistor	NPN	100mA	250mW	40V	100~300	3P/SOT-23
22807	PMBT3906	PHILIPS	PNP switching transistor	PNP	-100mA	250mW	-40V	100~300	3P/SOT-23
22809	PXTA14	PHILIPS	NPNDarlington transistor	NPN	500mA	1.3W	30V	20000	3P/SOT-89
22824	SMBT2222A	Infineon	NPN Silicon Switching Transistor	NPN	600mA	330mW	40V	35~300	3P/SOT-23
27417	UPA1520H	NEC	Compound Field Effect Power Transistor	NPN					10P/SIP
22821	UTC8050S	UTC	TO-92 Plastic-Encapsulate Transistors	NPN	0.5mA	0.625W	40V	85~300	3P/TO-92

J-FET/MOSFET 電晶體

2N-系列場效應電晶體

2N-Series J-FET Transistors

詳細產品規格--請點擊www.100y.com.tw



PartNo.	ProductNo.	Manuf.	Description	PoI	Vdgr	Vgss	Pd(max)	Id(max)	Pins/Package
4889	2N7000	MOT.	N-Channel Enhancement Mode Field Effect Transistor	N	60V	60V	400mW	200mA	3P/TO-92
23221	2N7000		N-Channel Enhancement Mode Field Effect Transistor	N	60V	60V	400mW	200mA	3P/TO-92
11972	2N7002-7	ON-Semi.	N-Channel Enhancement Mode Field Effect Transistor	N	60V	60V	200mW	115mA	3P/SOT-23
8236	MPF102	MOT.	JFET VHF Amplifier N-Channel-Depletion	N	25V	-25V	350mW	20mA	3P/TO-92

MTP-系列場效應電晶體

MTP-Series J-FET Transistors

詳細產品規格--請點擊www.100y.com.tw



Features

12A, 60V. $R_{DS(ON)} = 0.150 \Omega @ V_{GS} = 10V$
 Critical DC electrical parameters specified at elevated temperature.
 Rugged internal source-drain diode eliminates the need for an external Zener diode transient suppressor.
 175 maximum junction temperature rating.

PartNo.	ProductNo.	Description	PoI	Vdgr	Vgss	Pd(max)	Id(max)	Pins/Package
13148	MTP3055V	TRANSISTOR	N	60V	20V	48W	12A	3P/TO-220

2SJ-系列場效應電晶體

2SJ-Series J-FET Transistors

詳細產品規格--請點擊www.100y.com.tw



Recommended for First Stages of EQ Amplifiers and MC Head Amplifiers.
 High $|Y_{fs}|$: $|Y_{fs}| = 22mS (Typ.) (V_{DS} = -10V, V_{GS} = 0, I_{DSS} = -3mA)$
 Low Noise: $En = 0.95nV/\sqrt{Hz} (Typ.) (V_{DS} = -10V,$

$I_{DS} = 1mA, f = 1kHz)$
 High Input Impedance: $I_{GSS} = 1.0nA (Max.) (V_{GS} = 25V)$
 Complementary to 2SK370
 Small Package

PartNo.	ProductNo.	Manuf.	Description	PoI	Vdgr	Vgss	Pd(max)	Id(max)	Pins/Package
18465	2SJ108	TOSHIBA	JFET		25V		200mW	-10mA	3P/TO-92
14864	2SJ299L	HITACHI	MOSFET	P		-20V	20W	-5A	3P/TO-251 (I-PAK)

